

In the Abstract:

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Abstract of the Disclosure

A method for producing, on an SiC substrate, SiC homoepitaxial layers of the same polytype as the substrate. The layers are grown on a surface of the SiC substrate, wherein the surface is inclined relative to the (0001) basal plane at an angle higher than 0.1 degree but less than 1 degree. An homoepitaxial growth is started by forming a boundary layer with a thickness up to 1 μm .